

# **TSM4431**

#### 30V P-Channel MOSFET



SOP-8

#### Pin Definition:

- 1. Source
- 2. Source
- 3. Source
- 4. Gate
- 5, 6, 7, 8. Drain

#### PRODUCT SUMMARY

| V <sub>DS</sub> (V) | $R_{DS(on)}(m\Omega)$        | I <sub>D</sub> (A) |
|---------------------|------------------------------|--------------------|
| -30                 | 40 @ V <sub>GS</sub> = -10V  | -5.8               |
|                     | 70 @ V <sub>GS</sub> = -4.5V | -4.5               |

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

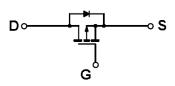
#### **Application**

- DC-DC Conversion
- Asynchronous Buck Converter

#### **Ordering Information**

| Part No.     | Package | Packing |
|--------------|---------|---------|
| TSM4431CS RL | SOP-8   | T&R     |

#### **Block Diagram**



P-Channel MOSFET

#### Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

| Parameter  |                           | Symbol                            | Limit        | Unit |
|--|---------------------------|-----------------------------------|--------------|------|
| Drain-Source Voltage                             |                           | V <sub>DS</sub>                   | -30          | V    |
| Gate-Source Voltage                              |                           | $V_{GS}$                          | ±20          | V    |
| Continuous Drain Current                         |                           | I <sub>D</sub>                    | -5.8         | Α    |
| Pulsed Drain Current                             |                           | I <sub>DM</sub>                   | -20          | Α    |
| Continuous Source Current (Diode Co              | onduction) <sup>a,b</sup> | Is                                | -2.3         | Α    |
| Maximum Power Dissipation                        | Ta = 25 °C                | - P <sub>D</sub>                  | 2.5          | W    |
|  | Ta = 75 °C                |                                   | 1.6          | VV   |
| Operating Junction Temperature                   |                           | TJ                                | +150         | °C   |
| Operating Junction and Storage Temperature Range |                           | T <sub>J</sub> , T <sub>STG</sub> | - 55 to +150 | °C   |

#### **Thermal Performance**

| Parameter  | Symbol           | Limit | Unit |  |  |
|--|------------------|-------|------|--|--|
| Junction to Case Thermal Resistance                  | R⊖ <sub>JC</sub> | 30    | °C/W |  |  |
| Junction to Ambient Thermal Resistance (PCB mounted) | RO <sub>JA</sub> | 50    | °C/W |  |  |

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 10$  sec.



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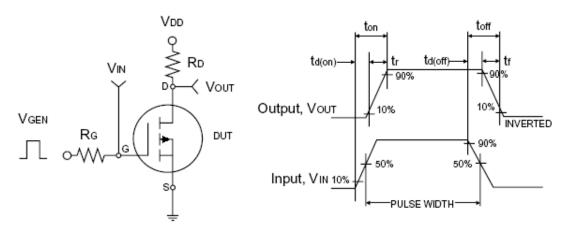
### 30V P-Channel MOSFET



**Electrical Specifications** 

| Parameter                                     | Conditions                                       | Symbol              | Min | Тур     | Max  | Unit |
|---|--|---------------------|-----|---------|------|------|
| Static  |  |                     |     |         |      |      |
| Drain-Source Breakdown Voltage                | $V_{GS} = 0V, I_D = -250uA$                      | BV <sub>DSS</sub>   | -30 |         |      | V    |
| Gate Threshold Voltage                        | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$            | $V_{GS(TH)}$        | -1  |         | -3   | V    |
| Gate Body Leakage                             | $V_{GS} = \pm 20V, V_{DS} = 0V$                  | I <sub>GSS</sub>    |     |         | ±100 | nA   |
| Zero Gate Voltage Drain Current               | $V_{DS} = -30V, V_{GS} = 0V$                     | I <sub>DSS</sub>    |     |         | 1.0  | μA   |
| On-State Drain Current <sup>a</sup>           | $V_{DS} \le -5V, V_{GS} = -4.5V$                 | $I_{D(ON)}$         | -7  |         |      | Α    |
| Drain Course On State Desigtance              | $V_{GS} = -10V, I_D = -5.8A$                     |                     | I   | 29      | 40   | mΩ   |
| Drain-Source On-State Resistance <sup>a</sup> | $V_{GS} = -4.5V$ , $I_D = -4.5A$                 | R <sub>DS(ON)</sub> | 1   | 47      | 70   |      |
| Forward Transconductance <sup>a</sup>         | $V_{DS} = -15V$ , $I_{D} = -5.3A$                | g <sub>fs</sub>     | 4   | 7       |      | S    |
| Diode Forward Voltage                         | $I_S = -2.3A$ , $V_{GS} = 0V$                    | $V_{SD}$            | 1   |         | -1.1 | V    |
| Dynamic <sup>b</sup>                          |  |                     |     |         |      |      |
| Total Gate Charge                             | $V_{DS} = -15V, I_{D} = -3.5A,$                  | $Q_g$               |     | 18.09   |      |      |
| Gate-Source Charge                            | $V_{DS} = -15V, I_D = -3.5A,$<br>$V_{GS} = -10V$ | $Q_gs$              |     | 6.52    |      | nC   |
| Gate-Drain Charge                             | V <sub>GS</sub> = -10V                           | $Q_{gd}$            | -   | 3.25    |      |      |
| Input Capacitance                             | \/ - 45\/ \/ - 0\/                               | $C_{iss}$           | -   | 1047.98 |      |      |
| Output Capacitance                            | $V_{DS} = -15V, V_{GS} = 0V,$<br>f = 1.0MHz      | C <sub>oss</sub>    | 1   | 172.82  |      | pF   |
| Reverse Transfer Capacitance                  | 1 - 1.0IVIDZ                                     | $C_{rss}$           |     | 115.50  |      |      |
| Switching <sup>c</sup>                        |  |                     |     |         |      |      |
| Turn-On Delay Time                            | V 45V D 450                                      | t <sub>d(on)</sub>  |     | 20.52   |      |      |
| Turn-On Rise Time                             | $V_{DD} = -15V, R_L = 15\Omega,$                 | t <sub>r</sub>      |     | 4.43    |      | 20   |
| Turn-Off Delay Time                           | $I_D = -1A$ , $V_{GEN} = -10V$ ,                 | t <sub>d(off)</sub> |     | 42.81   |      | nS   |
| Turn-Off Fall Time                            | $R_G = 6\Omega$                                  | t <sub>f</sub>      |     | 7.35    |      |      |

- a. pulse test: PW  $\leq 300 \mu S$ , duty cycle  $\leq 2\%$  b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms



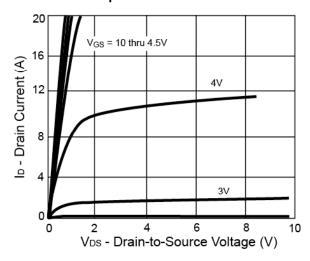




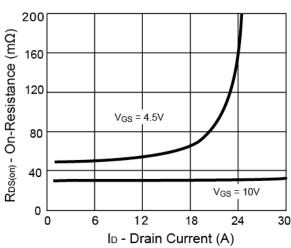


#### **Electrical Characteristics Curve** (Ta = 25 °C, unless otherwise noted)

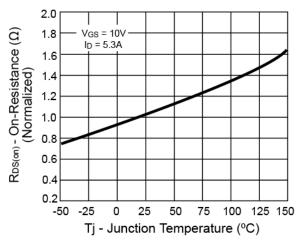
#### **Output Characteristics**



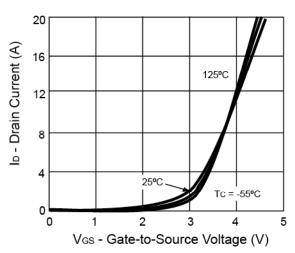
#### **On-Resistance vs. Drain Current**



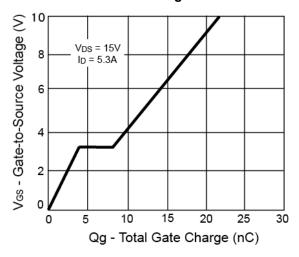
#### On-Resistance vs. Junction Temperature



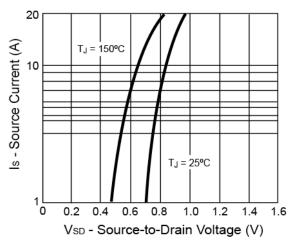
#### **Transfer Characteristics**



**Gate Charge** 



#### Source-Drain Diode Forward Voltage





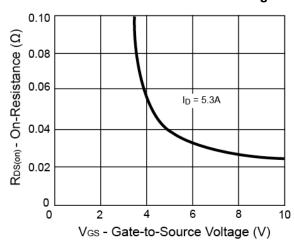


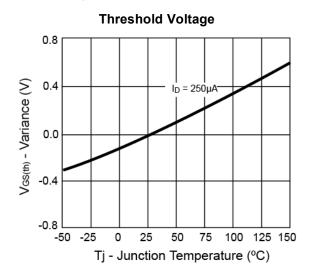




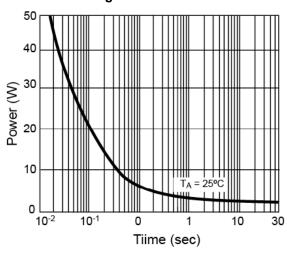
#### Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

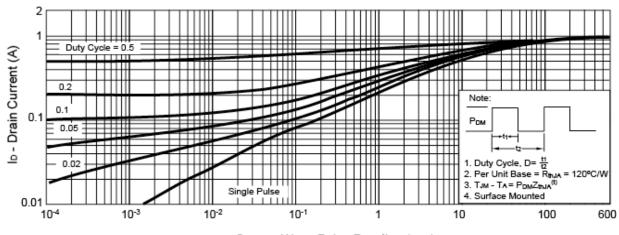




#### **Single Pulse Power**



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



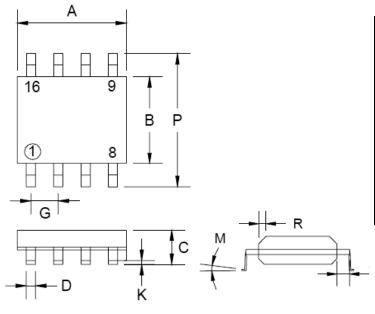
Square Wave Pulse Duration (sec)





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# **SOP-8 Mechanical Drawing**



| SOP-8 DIMENSION |             |      |        |       |  |
|-----------------|-------------|------|--------|-------|--|
| DIM             | MILLIMETERS |      | INCHES |       |  |
|                 | MIN         | MAX  | MIN    | MAX.  |  |
| Α               | 4.80        | 5.00 | 0.189  | 0.196 |  |
| В               | 3.80        | 4.00 | 0.150  | 0.157 |  |
| С               | 1.35        | 1.75 | 0.054  | 0.068 |  |
| D               | 0.35        | 0.49 | 0.014  | 0.019 |  |
| F               | 0.40        | 1.25 | 0.016  | 0.049 |  |
| G               | 1.27BSC     |      | 0.05   | BSC   |  |
| K               | 0.10        | 0.25 | 0.004  | 0.009 |  |
| М               | 0°          | 7°   | 0°     | 7°    |  |
| Р               | 5.80        | 6.20 | 0.229  | 0.244 |  |
| R               | 0.25        | 0.50 | 0.010  | 0.019 |  |



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